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***Optical and EUV
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Contents

vii *Conference Committee*

SESSION 2 EUV PRESENT AND FUTURE OUTLOOK

- 12051 02 EUV optics: status, outlook and future (Invited Paper) [12051-3]
- 12051 03 Role of ion accumulation in lofting of submicrometer-sized dielectric particle from dielectric surface by plasma and low-energy electron beam [12051-5]

SESSION 3 MASK

- 12051 04 Impact of mask variations on CD and placement in resist: local versus global effects [12051-11]

SESSION 4 EUV STOCHASTIC PRINTING

- 12051 05 Calibration of Gaussian random field stochastic EUV models [12051-14]
- 12051 07 Improvement of local CDU by using low speckle imaging [12051-17]

SESSION 5 ARF AND KRF SYSTEMS

- 12051 08 Technology development progress of digital scanner (Invited Paper) [12051-18]
- 12051 09 A novel solution on KrF pixel layer with thick photo resist (PR) by single exposure multi-focal imaging (SE MFI) technique [12051-22]

SESSION 6 MASK INSPECTION AND EUV PELLICLES

- 12051 0A AIMS EUV evolution towards high NA: challenge definition and solutions implementation [12051-25]
- 12051 0B High-transmission EUV pellicles supporting >400W source power [12051-26]

SESSION 7 NOVEL EUV MASK

- 12051 0C **Focus considerations of design pitches and absorber choice for EUV random logic (Invited Paper)** [12051-28]
- 12051 0D **Evaluation of Ta-Co alloys as novel high-k EUV mask absorber** [12051-30]
- 12051 0E **Characterizing EMA modelled EUV absorbers for high reflectivity: high phase performance** [12051-32]

SESSION 8 EUV STOCHASTICS: JOINT SESSION WITH CONFERENCES 12051 AND 12055

- 12051 0F **High NA EUV stochastic resist modeling considered with development parameters** [12051-34]

SESSION 9 PATTERNING

- 12051 0G **EUV and immersion lithography integration in 7nm FPGA production** [12051-36]
- 12051 0H **Investigation of low-n mask in 0.33 NA EUV single patterning at pitch 28nm metal design** [12051-37]
- 12051 0I **Logic via printability enhancement using restricted via placement and exhaustive SRAF placement on a staggered grid** [12051-38]

SESSION 12 EUV INTEGRATION: JOINT SESSION WITH CONFERENCE 12051 AND 12056

- 12051 0J **Orthogonal array pillar process development for high density 4F2 memory cells at 40nm pitch and beyond** [12051-45]

SESSION 13 OVERLAY

- 12051 0K **On-scanner high-spatial-frequency overlay control using a distortion manipulator** [12051-47]
- 12051 0L **On-product overlay solutions for DUV and EUV mix-scanner usage in an EPE-driven patterning world** [12051-48]

POSTER SESSION

- 12051 0N **Investigation of atomic emission from tin and heavier elements to heavier elements for further optimization and extension to shorter wavelength of the EUV sources** [12051-54]
- 12051 0O **Optimal thickness of phase shift mask considering phase and reflectance in high NA EUV contact-hole pattern** [12051-55]
- 12051 0P **EUV low-n attenuated phase-shift mask on random logic via single patterning at pitch 36nm** [12051-56]
- 12051 0Q **Pattern customization on 193 immersion lithography by negative tone development process and multiple exposures** [12051-57]
- 12051 0R **Integrated simulations of hybrid discharge-laser produced plasma devices for EUV metrology** [12051-59]
- 12051 0T **Key technology development progress of the high power LPP-EUV light source** [12051-68]
- 12051 0U **Simulation of a discharge produced plasma (DPP) for Blue-X (6.x nm) EUV radiation** [12051-85]